

isc Silicon PNP Power Transistor

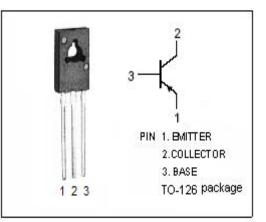
BD726

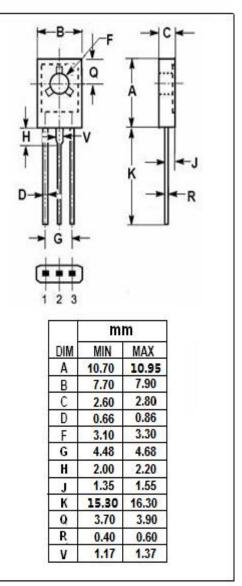
DESCRIPTION

- DC Current Gain-
- : h_{FE}= 40@ I_C= -0.5A
- Collector-Emitter Breakdown Voltage -
- : V_{(BR)CEO}= -120V(Min)
- Complement to type BD725
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

• Designed for use in audio output and general purpose amplifier applications.





ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT		
V _{CBO}	Collector-Base Voltage	-120	V		
VCEO	Collector-Emitter Voltage -		V		
V _{EBO}	Emitter-Base Voltage		V		
Ic	Collector Current-Continuous -4		А		
I _{CM}	Collector Current-Peak		А		
I _B	Base Current-Continuous -		А		
Pc	$\begin{tabular}{ c c c c c } \hline Collector Power Dissipation \\ @ T_c=25 \end{tabular} C \end{tabular} 36 \end{tabular}$		W		
TJ	Junction Temperature 150		°C		
T _{stg}	Storage Temperature Range	-65~150	°C		

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	3.5	°C/W
R _{th j-a}	Thermal Resistance, Junction to Ambient	100	°C/W



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ELECTRICAL CHARACTERISTICS

$T_{\texttt{C}}\text{=}25^{\circ}\!\!\!\mathbb{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA ; I _B = 0	-120			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -2A; I _B = -0.2A			-1.0	V
$V_{\text{BE(on)}}$	Base-Emitter On Voltage	I _C = -2A; V _{CE} = -4V			-1.4	v
І _{сво}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-50	μA
		V _{CB} = -60V; I _E = 0; T _C = 150℃			-1	mA
I _{CEO}	Collector Cutoff Current	V _{CE} = -60V; I _B = 0			-0.1	mA
Іево	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-0.2	mA
h _{FE-1}	DC Current Gain	I _C = -0.5A; V _{CE} = -4V	40			
h _{FE-2}	DC Current Gain	I _C = -2A; V _{CE} = -4V	20			
f _T	Current-Gain—Bandwidth Product	I _C = -0.5A; V _{CE} = -4V	3			MHz

Switching Times

t _{on}	Turn-On time	I_{C} = -1A; I_{B1} = - I_{B2} = -0.1A; V _{CC} = -20V	0.1	μs
t _{off}	Turn-Off time		0.4	μ S

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